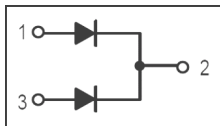


Ultrafast Recovery Diode in a TO-220F Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 Anode PIN 2 Cathode PIN 3 Anode

See Marking Instructions

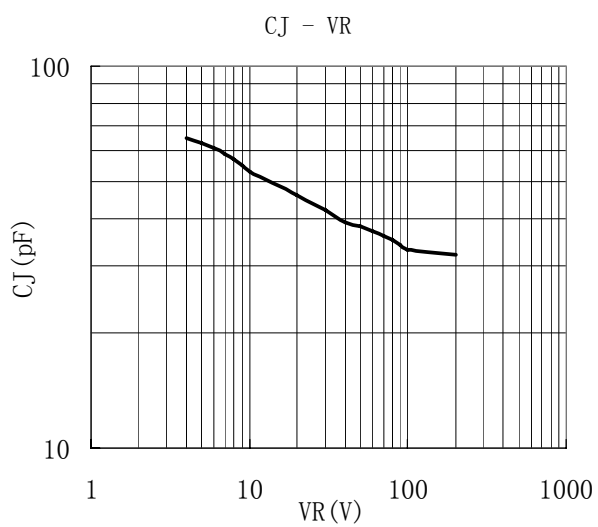
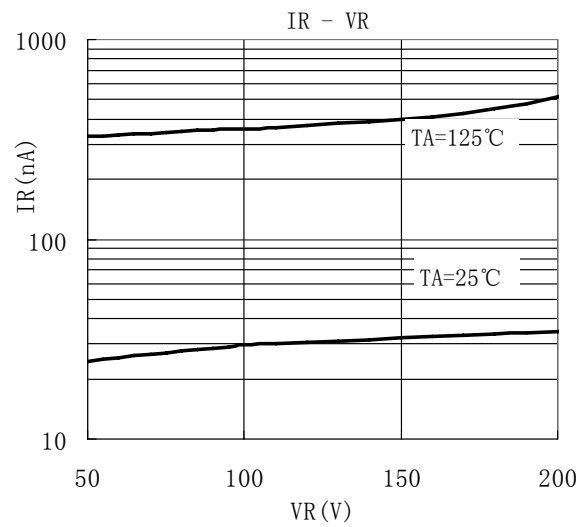
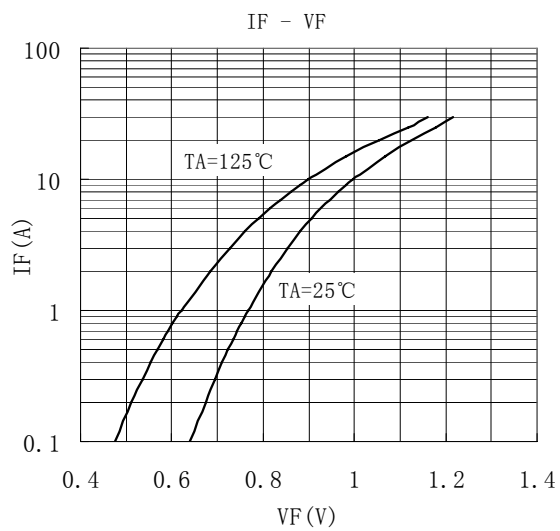
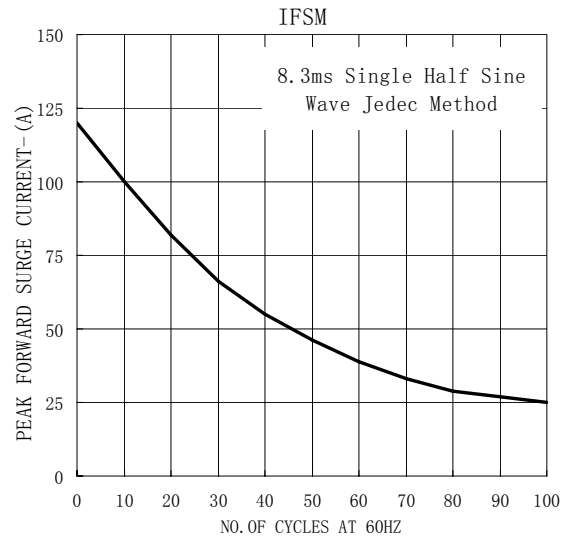
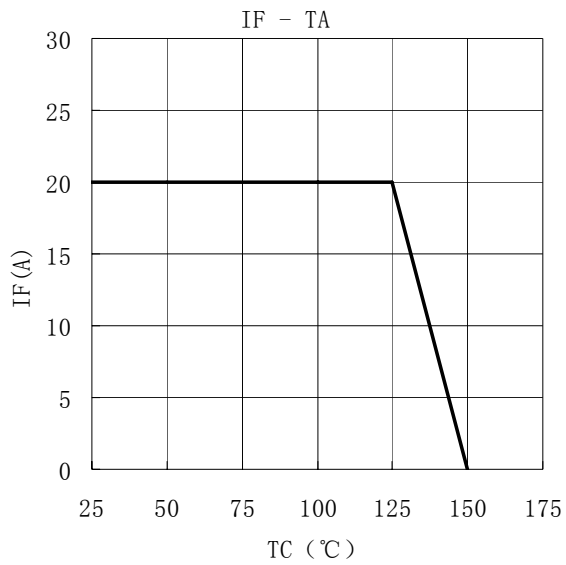
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Forward Current	I_F	2×6	A
Non Repetitive Peak Surge Current	I_{FSM}	100	A
Thermal Resistance Junction to Case	R_{JC}	3.3	/W
Storage Temperature Range	$T_j T_{stg}$	-55~150	

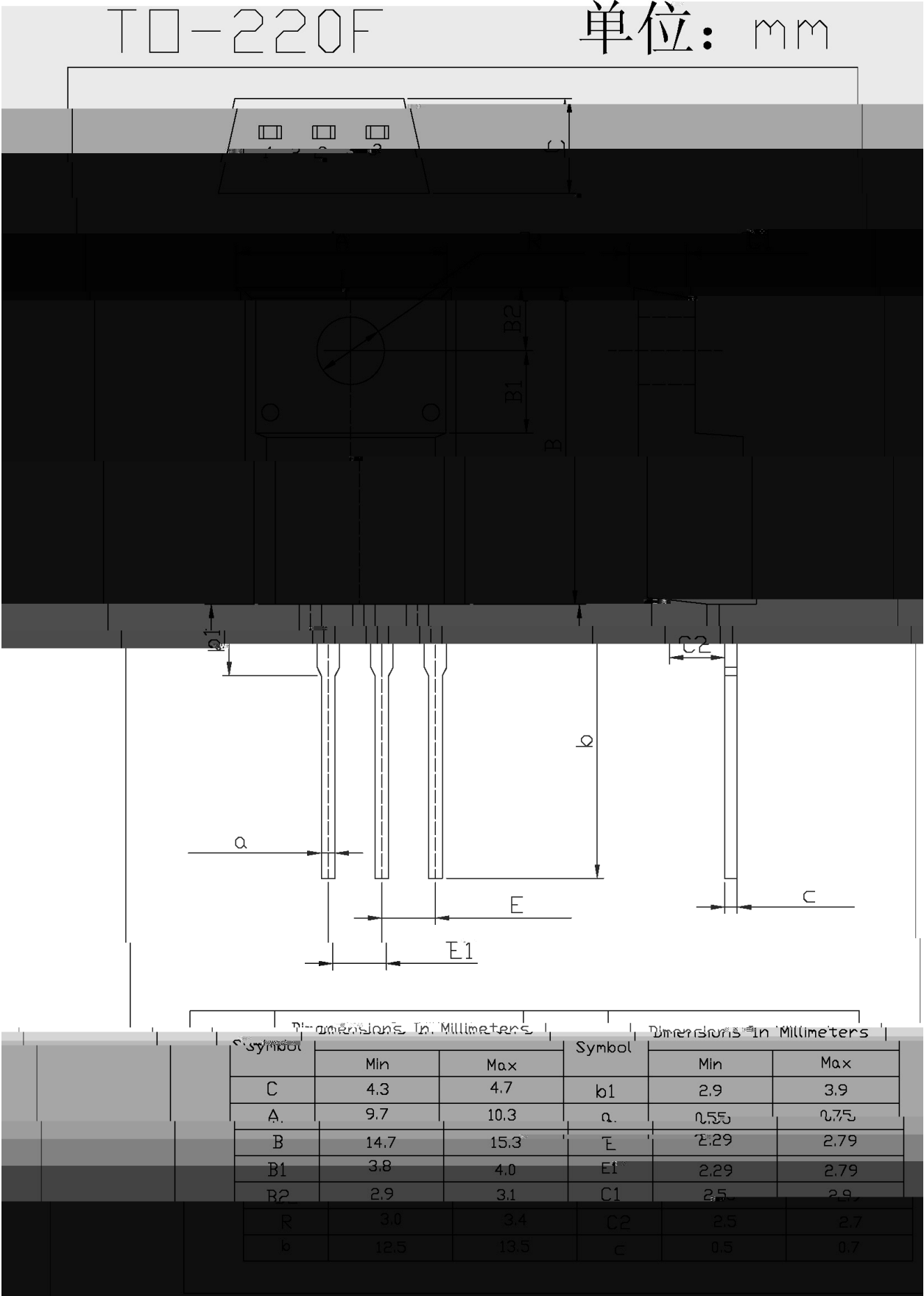
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=2A \quad T_c=25$		0.82		V
		$I_F=2A \quad T_c=125$		0.68		V
		$I_F=6A \quad T_c=25$		0.92	1.0	V
		$I_F=6A \quad T_c=125$		0.82	0.9	V
Instantaneous Reverse Current	I_R	$V_R=200V \quad T_a=25$			10	A
		$V_R=200V \quad T_a=125$			150	A
Reverse Recovery Time	t_{rr}	$I_R=1.0A, \quad I_{RR}=0.25A$ $I_F=0.5A$			35	ns

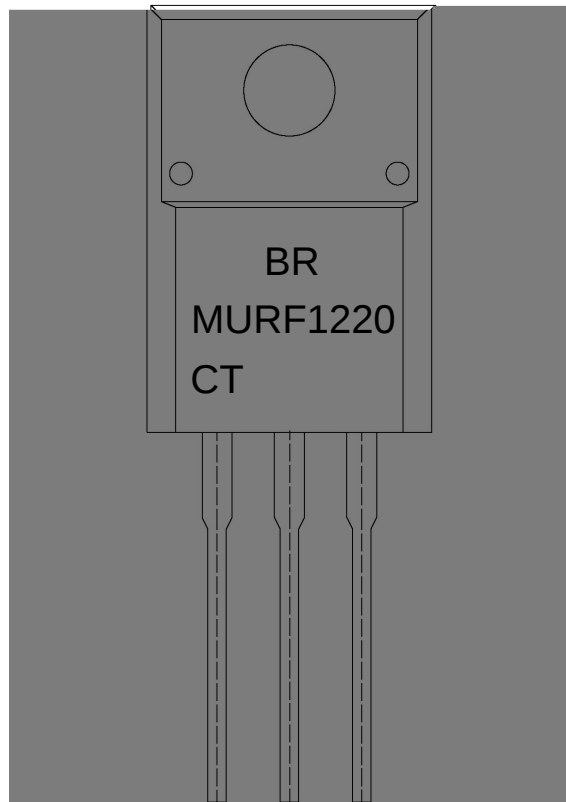
/Notes:

effect.

2. . / Unless otherwise noted, values for the parameters of a single chip







Note:

BR: Company Code

MURF1220: Product Type.

CT: Internal Structure

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱